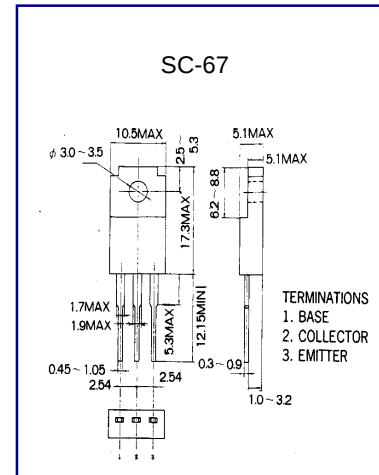


**2SC5416LS****NPN SILICON TRANSISTOR****HIGH VOLTAGE POWER
SWITCHING APPLICATIONS****ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE0}	1000	V
Collector-Emitter Voltage	V_{CEO}	450	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current (DC)	I_C	4	A
Collector Current (Pulse)	I_C	8	A
Base Current (DC)	I_B	2	A
Base Current (Pulse)	I_B	4	A
Collector Dissipation ($T_C=25^{\circ}\text{C}$)	P_C	100	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-65~150	$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CE0(SUS)}$	$I_C=100\text{mA}$, $I_B=0$	450			V
Collector Cutoff Current	I_{CES}	$V_{CE}=850\text{V}$, $V_{EB}=0$ $V_{CE}=1000\text{V}$, $V_{EB}=0$			1 1	mA mA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=9\text{V}$, $I_C=0$			10	μA
DC Current Gain	h_{FE}	$I_C=0.1\text{A}$, $V_{CE}=5\text{V}$	30		50	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.5\text{A}$, $I_B=0.5\text{A}$			1.5	V
Fall Time	t_f				0.15	μS